

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (DARLINGTON POWER)

2SD1409A

IGNITER APPLICATIONS.

HIGH VOLTAGE SWITCHING APPLICATIONS.

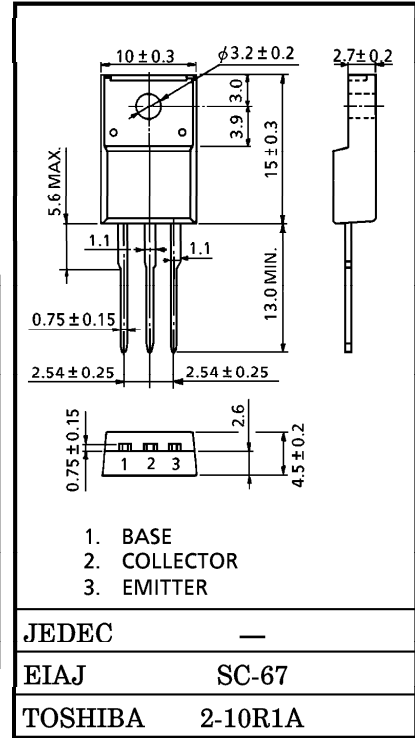
- High DC Current Gain : $h_{FE} = 600$ (Min.) ($V_{CE} = 2V, I_C = 2A$)
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	6	A
Base Current		I_B	1	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	2.0	W
	$T_c = 25^\circ C$		25	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

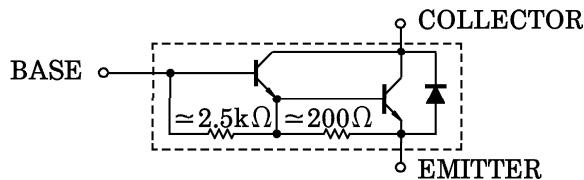
INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 1.7g

EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 600V, I _E = 0	—	—	0.5	mA
Emitter Cut-off Current		IEBO	V _{EB} = 5V, I _C = 0	—	—	3	mA
Collector-Emitter Breakdown Voltage		V (BR) CBO	I _C = 10mA, I _B = 0	400	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 2V, I _C = 2A	600	—	—	
		h _{FE} (2)	V _{CE} = 2V, I _C = 4A	100	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 4A, I _B = 0.04A	—	—	2.0	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 4A, I _B = 0.04A	—	—	2.5	V
Emitter-Collector Forward Voltage		V _{ECF}	I _E = 4A, I _B = 0	—	—	3.0	V
Collector Output Capacitance		C _{ob}	V _{CB} = 50V, I _E = 0, f = 1MHz	—	35	—	pF
Switching Time	Turn-on Time	t _{on}	<p>IN- PUT</p> <p>OUTPUT</p> <p>20 μs</p> <p>I_{B1}</p> <p>I_{B2}</p> <p>V_{CE}</p> <p>V_{CC} = 100V</p>	—	1	—	μs
	Storage Time	t _{stg}		—	8	—	
	Fall Time	t _f		—	5	—	

